



COPY OF PAPERS  
ORIGINALLY FILED

Docket No.: GR 98 P 2499 P

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231, on the date indicated below.

By: Markus Noll

Date: August 6, 2002

Inventor : Thomas Peter Haneder et al.  
Applic. No. : 09/801,209  
Filed : March 7, 2001  
Title : Ferroelectric Transistor, Use Thereof In A Memory Cell  
Configuration And Method Of Producing The Ferroelectric  
Transistor  
Examiner : Thao X. Le - Art Unit: 2814

RECEIVED  
AUG 23 2002  
TECHNOLOGY CENTER 2800

## RESPONSE

Hon. Commissioner of Patents and Trademarks,  
Washington, D. C. 20231

Sir:

Responsive to the Office Action dated July 26, 2002, the following remarks are made:

In deference to the restriction requirement on pages 2 and 3 of the above-identified Office Action, applicants elect **group I**, claims 1-12 for prosecution at this time.

Applicants reserve the right to file a divisional application including the method claims of **group II** at a later date and/or to request a rejoinder under MPEP §821.04.

In view of the foregoing, the early issuance of an Action on the merits of claims is solicited.

Respectfully submitted,

Markus Noll  
For Applicants

MARKUS NOLFF  
REG. NO. 37,006

Date: August 6, 2002

Lerner and Greenberg  
Post Office Box 2480  
Hollywood, FL 33022-2480  
Tel: (954) 925-1100  
Fax: (954) 925-1101

/kf